

SOT23 NPN SILICON PLANAR
HIGH VOLTAGE TRANSISTOR

ISSUE 2 – SEPTEMBER 95



BSS64

咨询"BSS64-U3"供应商



COMPLIMENTARY TYPE - BSS63

PARTMARKING DETAIL - BSS64 - U3
BSS64R - U6

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	120	V
Collector-Emitter Voltage	V_{CEO}	80	V
Emitter-Base Voltage	V_{EBO}	5	V
Continuous Collector Current	I_C	100	mA
Power Dissipation at $T_{amb}=25^{\circ}\text{C}$	P_{TOT}	330	mW
Operating and Storage Temperature Range	t_j, t_{stg}	-55 to +150	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$).

PARAMETER	SYMBOL	MIN.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	120		V	$I_C=100\mu\text{A}$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	80		V	$I_C=4\text{mA}$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	5		V	$I_E=100\mu\text{A}$
Collector Cut-Off Current	I_{CBO}		100 50	nA μA	$V_{CB}=90\text{V}, T_j=150^{\circ}\text{C}$
Emitter Cut-Off Current	I_{EBO}		200	nA	$V_{EB}=5\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		150 200	mV mV	$I_C=4\text{mA}, I_B=400\mu\text{A}$ $I_C=50\text{mA}, I_B=15\text{mA}$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		1.2	mV	$I_C=4\text{mA}, I_B=400\mu\text{A}$
Static Forward Current	h_{FE}	20	Typ. 60 80 55		$I_C=1\text{mA}, V_{CE}=1\text{V}$ $I_C=10\text{mA}, V_{CE}=1\text{V}$ $I_C=20\text{mA}, V_{CE}=1\text{V}$
Transition Frequency	f_T	60	Typ. 100	MHz	$V_{CE}=10\text{V}, I_C=4\text{mA}$ $f=35\text{ MHz}$
Output Capacitance	C_{obo}	Typ. 3	5	pF	$V_{CB}=10\text{V}, f=1\text{MHz}$

* Measured under pulsed conditions. Pulse width=300 μs . Duty cycle $\leq 2\%$